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Zagotavljanje kakovosti proizvodov v vesoljski tehniki - Priročnik za tehnike blaženja učinkov sevanja na vezja ASIC in FPGA

Space product assurance - Techniques for radiation effects mitigation in ASICs and FPGAs handbook

Raumfahrtproduksicherung - Handbuch zu Minderungsmethoden von Strahlungseffekten auf ASICs und FPGAs

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Ingénierie spatiale - Guide sur les techniques de durcissement des ASICs et FPGAs vis-à-vis des effets des radiations

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durcissement des ASICs et FPGAs vis-à-vis des effets
des radiations

Raumfahrtproduksicherung - Handbuch zu
Minderungsmethoden von Strahlungseffekten auf
ASICs und FPGAs

This draft Technical Report is submitted to CEN members for Vote. It has been drawn up by the Technical Committee
CEN/CLC/JTC 5.

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